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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): T. SAITO et al

Serial No.: 09/850,162

Filed: May 8, 2001

For: A SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE  
AND A METHOD OF MANUFACTURING THE SAME

Group: 2812

Examiner: R. E. POMPEY

RECEIVED  
APR 17 2003  
TECHNOLOGY CENTER 2000**FURTHER SUPPLEMENTING AMENDMENT**Assistant Commissioner of Patents  
Washington, D. C. 20231

Oct. 10, 2002

Sir:

As a follow-up to the responsive Amendment filed on September 3, 2002 and further to the first Supplementing Amendment, filed on September 12, 2002, the following additional amendments and remarks are respectfully submitted in connection with the above-identified application.

**IN THE CLAIMS:**

Please amend claims 13. as follows:

13. (Amended) A method for manufacturing a semiconductor integrated circuit device according to Claim 12, wherein said diffusion-preventing insulating film is made of a silicon nitride film, a PSG film, or a carbon-containing silicon-based insulating film including a silicon carbide (SiC) film or a SiCO film.